

FIG. 1

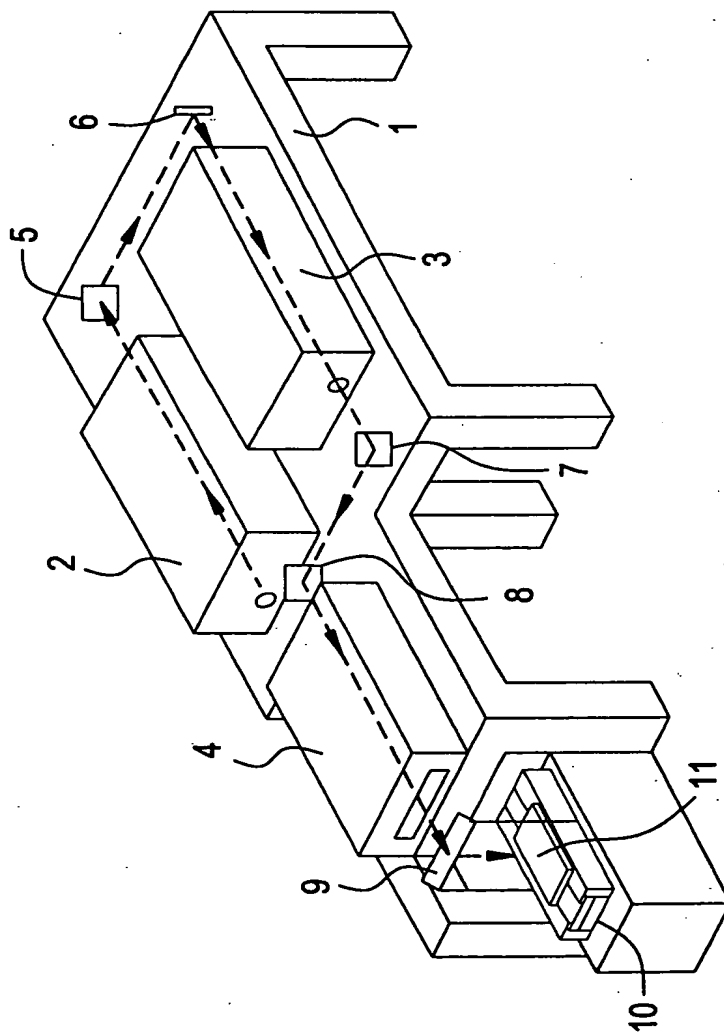
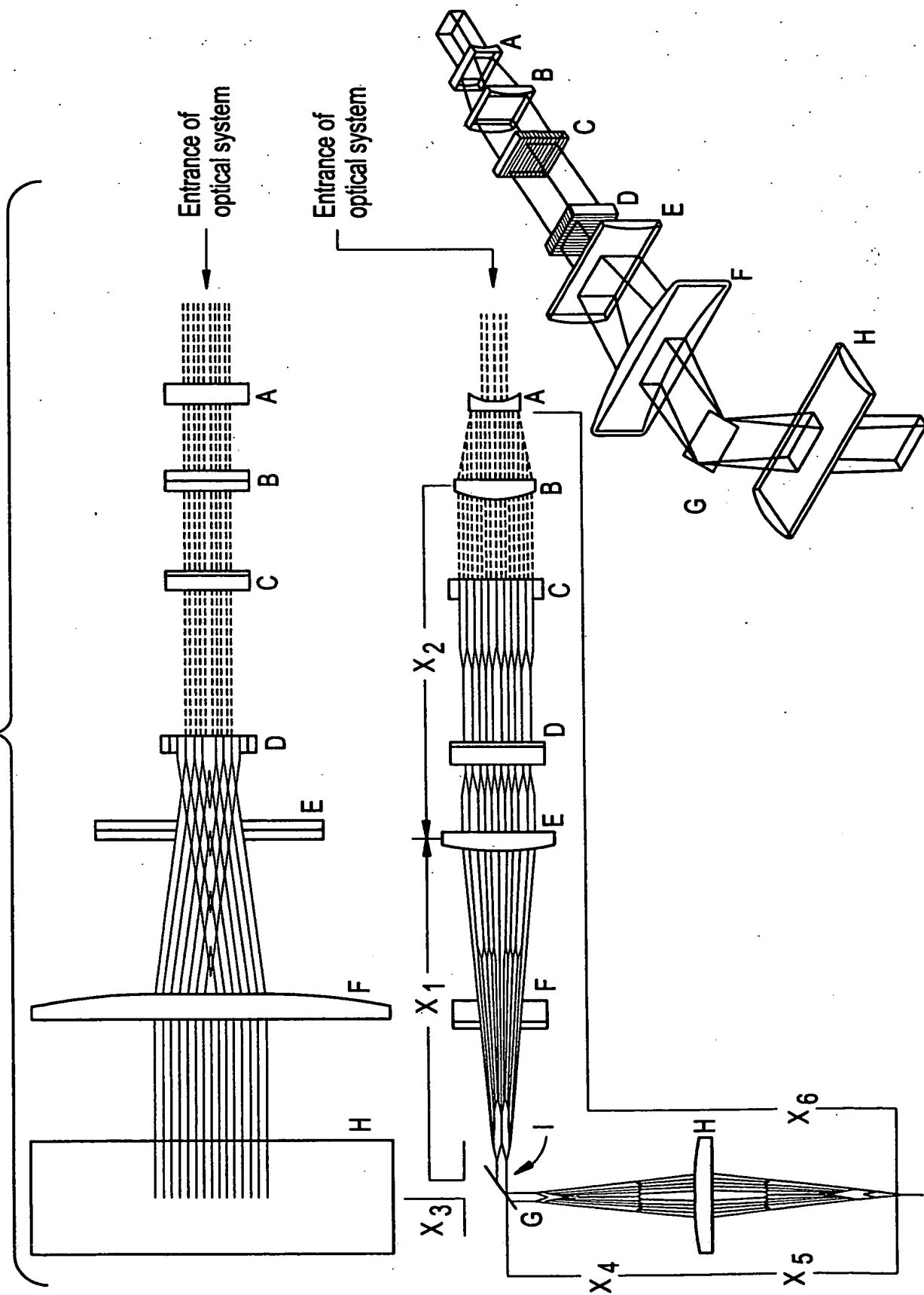


FIG. 2



2040T0" THSEOT

**FIG. 3**  
PRIOR ART

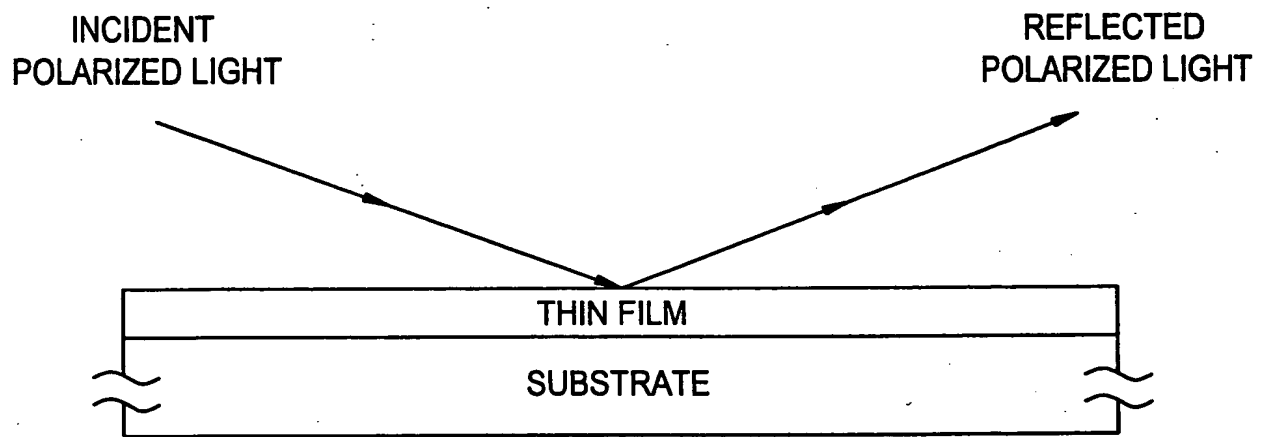


FIG. 4

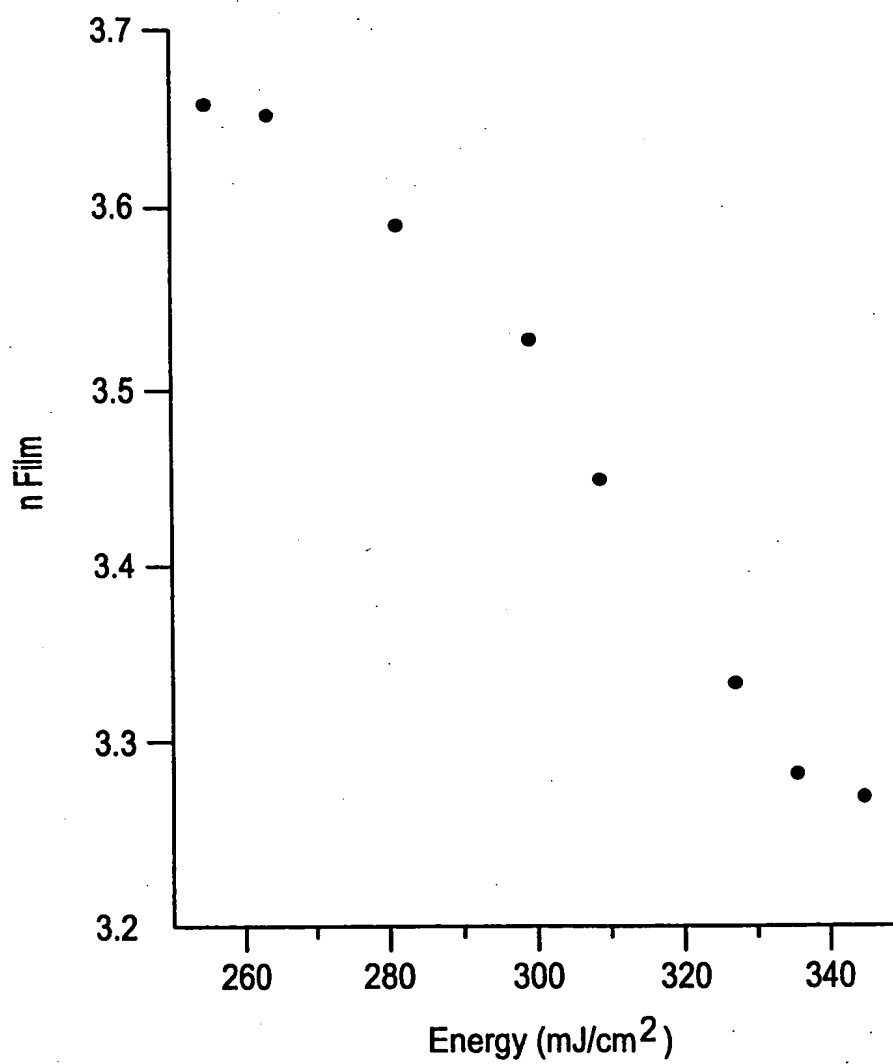


FIG. 5A

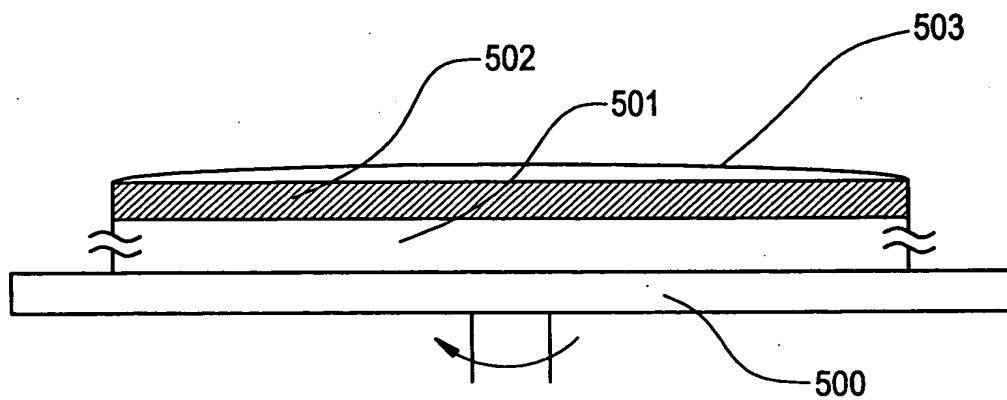


FIG. 5B

LASER LIGHT IRRADIATION

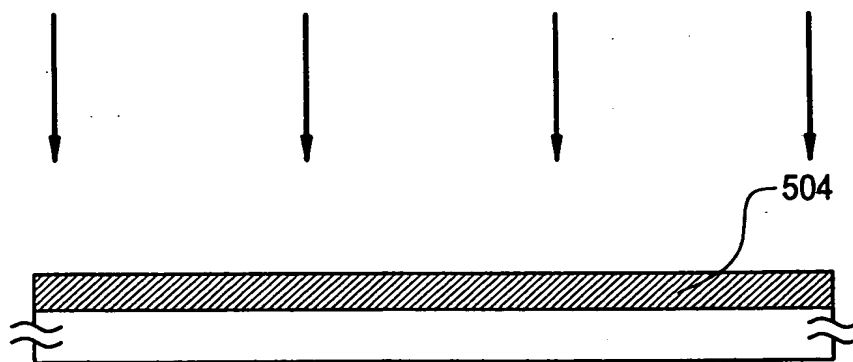


FIG. 5C

IMPURITY ION IMPLANTATION AND LASER LIGHT IRRADIATION

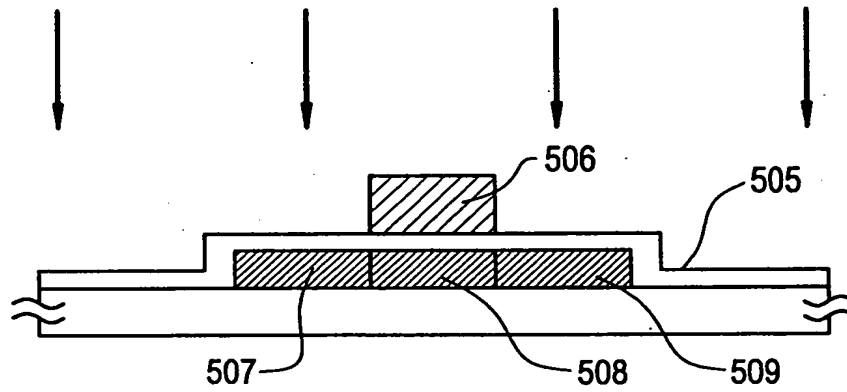
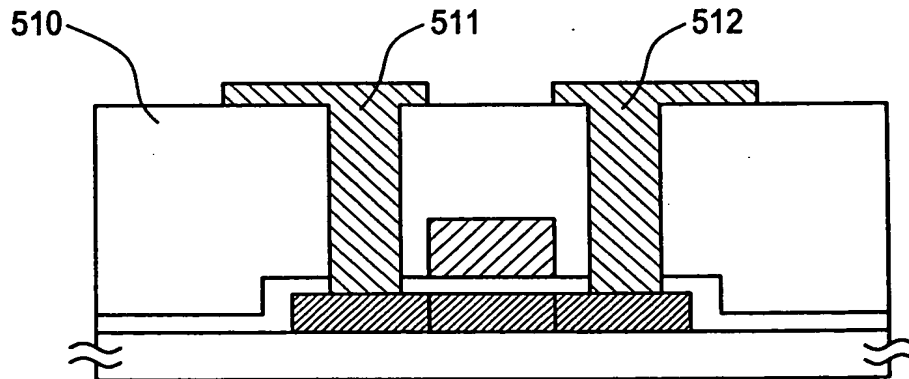


FIG. 5D



## FIG. 6A

IRRADIATING LASER LIGHT TO ONE GLASS  
SUBSTRATE FORMED ON CRYSTALLINE  
SILICON FILM



## FIG. 6B

MEASURING REFRACTIVE INDEX OF CRYSTALLINE  
SILICON FILM TO WHICH LASER  
LIGHT HAS BEEN IRRADIATED, BY ELLIPSOMETRY



## FIG. 6C

INCREASING IRRADIATION ENERGY OF LASER  
LIGHT, IN CASE THAT REFRACTIVE INDEX  
OBTAINED BY THE FOREGOING IS LARGER  
THAN PRESCRIBED REFRACTIVE INDEX



BACK TO FIG. 6A

**FIG. 7A**

# IRRADIATING LASER LIGHT TO SOURCE/DRAIN REGION OF THIN FILM TRANSISTOR FORMED ON GLASS SUBSTRATE TO PERFORM ANNEALING

**FIG. 7B**

IRRADIATING LASER LIGHT TO CRYSTALLINE SILICON  
FILM EVERY AFTER COMPLETING TREATMENT FOR  
ONE SUBSTRATE, AND MEASURING REFRACTIVE  
INDEX OF CRYSTALLINE SILICON FILM AFTER  
IRRADIATION, BY ELLIPSOMETRY

**FIG. 7C**

INCREASING IRRADIATION ENERGY OF LASER LIGHT IN CASE THAT THE FOREGOING REFRACTIVE INDEX IS LARGER THAN PRESCRIBED VALUE, AND DECREASING IRRADIATION ENERGY OF LASER LIGHT IN CASE THAT THE FOREGOING REFRACTIVE INDEX IS SMALLER THAN THE PRESCRIBED VALUE

**BACK TO FIG.7A**